

**In the claims:**

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Claims 1 to 11 (canceled)

Claim 12 (currently amended) the method of claim ~~11~~ 20 wherein the desired portion of the substrate comprises an area within the insulator layer and proximal to the outer edge.

J1  
Claim 13 (currently amended) The method of claim ~~11~~ 20 wherein the buffer material further comprises a material implanted between the lower bulk silicon layer and the upper silicon layer.

Claim 14 (original) The method of claim 13 wherein the buffer material is adapted to block mobile charge ingress.

Claim 15 (original) The method of claim 13 wherein the buffer material is adapted to trap mobile charges.

Claim 16 (original) The method of claim 13 wherein the buffer material is adapted to repel mobile charges.

Claim 17 (original) The method of claim 14 wherein the material implanted comprises nitrogen.

Claim 18 (original) The method of claim 15 wherein the material implanted comprises phosphorous.

Claim 19 (original) The method of claim 13 further comprising the step of annealing the buffer material after implantation.

Claim 20 (currently amended) A method of limiting mobile charge ingress within an SOI substrate, comprising the steps of:

providing an SOI substrate having an outer edge;

J<sub>1</sub> applying a mask to the substrate to form an apertures over a ~~desired~~ scribe area portions of the substrate ~~near the outer edge~~;

implanting a buffer material, selected to impede mobile charge ingress, through the aperture into the insulator layer within the substrate; ~~and~~

annealing the buffer material; and

then scribing said substrate along said apertures.

Claim 21 (new) The method of claim 20 further including the step of then forming devices within said apertures subsequent to said step of annealing.

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